

## MM54HC20/MM74HC20 Dual 4-Input NAND Gate

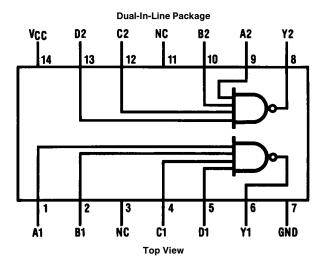
## **General Description**

These NAND gates utilize advanced silicon-gate CMOS technology to achieve operating speeds similar to LS-TTL gates with the low power consumption of standard CMOS integrated circuits. All gates have buffered outputs. All devices have high noise immunity and the ability to drive 10 LS-TTL loads. The 54HC/74HC logic family is functionally as well as pin-out compatible with the standard 54LS/74LS logic family. All inputs are protected from damage due to static discharge by internal diode clamps to  $V_{\rm CC}$  and ground.

#### **Features**

- Typical propagation delay: 8 ns
- Wide power supply range: 2-6V
- Low quiescent current: 20 µA maximum (74HC Series)
- Low input current: 1 µA maximum
- Fanout of 10 LS-TTL loads

## **Connection and Logic Diagrams**



TL/F/5299-1

Order Number MM54HC20 or MM74HC20

TL/F/5299-2

# Absolute Maximum Ratings (Notes 1 & 2)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

Supply Voltage (V <sub>CC</sub> )	-0.5 to $+7.0$ V
DC Input Voltage (V <sub>IN</sub> )	$-1.5$ to $V_{CC} + 1.5V$
DC Output Voltage (V <sub>OUT</sub> )	$-0.5$ to $V_{\rm CC} + 0.5V$
Clamp Diode Current (I <sub>IK</sub> , I <sub>OK</sub> )	$\pm$ 20 mA
DC Output Current, per pin (I <sub>OUT</sub> )	$\pm$ 25 mA
DC V <sub>CC</sub> or GND Current, per pin (I <sub>CC</sub> )	$\pm$ 50 mA
Storage Temperature Range (T <sub>STG</sub> )	-65°C to +150°C

Power Dissipation (PD)

(Note 3) 600 mW S.O. Package only 500 mW 260°C

Lead Temp. ( $T_L$ ) (Soldering 10 seconds)

## **Operating Conditions**

	•			
		Min	Max	Units
Supply Vo	oltage (V <sub>CC</sub> )	2	6	V
DC Input (V <sub>IN</sub> , V	or Output Voltage OUT)	0	$V_{CC}$	V
Operating	g Temp. Range (T <sub>A</sub> )			
MM74H	HC	-40	+85	°C
MM54H	HC	-55	+125	°C
Input Rise	e or Fall Times			
$(t_r, t_f)$	$V_{CC} = 2.0V$		1000	ns
	$V_{CC} = 4.5V$		500	ns
	$V_{CC} = 6.0V$		400	ns

### **DC Electrical Characteristics** (Note 4)

Symbol	Parameter	Conditions	nditions V <sub>CC</sub> T <sub>A</sub> =25°C		= 25°C	74HC T <sub>A</sub> = -40 to 85°C	54HC T <sub>A</sub> = -55 to 125°C	Units	
				Typ Guaranteed Limits					
V <sub>IH</sub>	Minimum High Level Input Voltage		2.0V 4.5V 6.0V		1.5 3.15 4.2	1.5 3.15 4.2	1.5 3.15 4.2	V V	
V <sub>IL</sub>	Maximum Low Level Input Voltage**		2.0V 4.5V 6.0V		0.5 1.35 1.8	0.5 1.35 1.8	0.5 1.35 1.8	V V V	
V <sub>OH</sub>	Minimum High Level Output Voltage	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $ I_{OUT}  \le 20 \mu A$	2.0V 4.5V 6.0V	2.0 4.5 6.0	1.9 4.4 5.9	1.9 4.4 5.9	1.9 4.4 5.9	V V V	
		$V_{IN} = V_{IH} \text{ or } V_{IL}$ $ I_{OUT}  \le 4.0 \text{ mA}$ $ I_{OUT}  \le 5.2 \text{ mA}$	4.5V 6.0V	4.2 5.7	3.98 5.48	3.84 5.34	3.7 5.2	V	
V <sub>OL</sub>	Maximum Low Level Output Voltage	V <sub>IN</sub> =V <sub>IH</sub>  I <sub>OUT</sub>  ≤20 μA	2.0V 4.5V 6.0V	0 0 0	0.1 0.1 0.1	0.1 0.1 0.1	0.1 0.1 0.1	V V V	
		$V_{IN} = V_{IH}$ $ I_{OUT}  \le 4.0 \text{ mA}$ $ I_{OUT}  \le 5.2 \text{ mA}$	4.5V 6.0V	0.2 0.2	0.26 0.26	0.33 0.33	0.4 0.4	V V	
I <sub>IN</sub>	Maximum Input Current	V <sub>IN</sub> =V <sub>CC</sub> or GND	6.0V		±0.1	±1.0	±1.0	μΑ	
Icc	Maximum Quiescent Supply Current	V <sub>IN</sub> =V <sub>CC</sub> or GND I <sub>OUT</sub> =0 μA	6.0V		2.0	20	40	μΑ	

Note 1: Absolute Maximum Ratings are those values beyond which damage to the device may occur.

Note 2: Unless otherwise specified all voltages are referenced to ground.

Note 3: Power Dissipation temperature derating — plastic "N" package: -12 mW/°C from 65°C to 85°C; ceramic "J" package: -12 mW/°C from 100°C to 125°C.

Note 4: For a power supply of 5V  $\pm 10\%$  the worst case output voltages (V<sub>OH</sub>, and V<sub>OL</sub>) occur for HC at 4.5V. Thus the 4.5V values should be used when designing with this supply. Worst case V<sub>IH</sub> and V<sub>IL</sub> occur at V<sub>CC</sub>=5.5V and 4.5V respectively. (The V<sub>IH</sub> value at 5.5V is 3.85V.) The worst case leakage current (I<sub>IN</sub>, I<sub>CC</sub>, and I<sub>OZ</sub>) occur for CMOS at the higher voltage and so the 6.0V values should be used.

<sup>\*\*</sup> $V_{IL}$  limits are currently tested at 20% of  $V_{CC}$ . The above  $V_{IL}$  specification (30% of  $V_{CC}$ ) will be implemented no later than Q1, CY'89.

## AC Electrical Characteristics $v_{CC}\!=\!5\text{V},\,T_{A}\!=\!25^{\circ}\text{C},\,C_{L}\!=\!15\,\text{pF},\,t_{r}\!=\!t_{f}\!=\!6\,\text{ns}$

Symbol	Parameter	Conditions	Тур	Guaranteed Limit	Units
t <sub>PHL</sub> , t <sub>PLH</sub>	Maximum Propagation Delay		8	15	ns

## $\textbf{AC Electrical Characteristics} \ \ V_{CC} = 2.0 \ \ \text{to 6.0V}, \ C_L = 50 \ \ \text{pF}, \ t_f = t_f = 6 \ \text{ns (unless otherwise specified)}$

Symbol	Parameter	Conditions	v <sub>cc</sub>	T <sub>A</sub> =25°C		74HC T <sub>A</sub> = -40 to 85°C	54HC T <sub>A</sub> = -55 to 125°C	Units
				Тур	Guaranteed Limits			
t <sub>PHL</sub> , t <sub>PLH</sub>	Maximum Propagation Delay		2.0V 4.5V 6.0V	45 9 8	90 18 15	113 23 19	134 27 23	ns ns ns
t <sub>TLH</sub> , t <sub>THL</sub>	Maximum Output Rise and Fall Time		2.0V 4.5V 6.0V	30 8 7	75 15 13	95 19 16	110 22 19	ns ns ns
C <sub>PD</sub>	Power Dissipation Capacitance (Note 5)	(per gate)		20				pF
C <sub>IN</sub>	Maximum Input Capacitance			5	10	10	10	pF

 $\textbf{Note 5:} \ \ C_{PD} \ \ \text{determines the no load dynamic power consumption, } \ P_D = C_{PD} \ V_{CC}^2 \ f + I_{CC} \ V_{CC}, \ \text{and the no load dynamic current consumption, } I_S = C_{PD} \ V_{CC} \ f + I_{CC} \ V_{CC}, \ \text{and the no load dynamic current consumption, } I_S = C_{PD} \ V_{CC} \ f + I_{CC} \ V_{CC}, \ \text{and the no load dynamic current consumption, } I_S = C_{PD} \ V_{CC} \ f + I_{CC} \ V_{CC}, \ \text{and the no load dynamic current consumption, } I_S = C_{PD} \ V_{CC} \ f + I_{CC} \ V_{CC}, \ \text{and the no load dynamic current consumption, } I_S = C_{PD} \ V_{CC} \ f + I_{CC} \ V_{CC}, \ \text{and the no load dynamic current consumption, } I_S = C_{PD} \ V_{CC} \ f + I_{CC} \ V_{CC}, \ \text{and the no load dynamic current consumption, } I_S = C_{PD} \ V_{CC} \ f + I_{CC} \ V_{CC}, \ \text{and the no load dynamic current consumption, } I_S = C_{PD} \ V_{CC} \ f + I_{CC} \ V_{CC}, \ \text{and the no load dynamic current consumption, } I_S = C_{PD} \ V_{CC} \ f + I_{CC} \ V_{CC}, \ \text{and the no load dynamic current consumption, } I_S = C_{PD} \ V_{CC} \ f + I_{CC} \ V_{CC}, \ \text{and the no load dynamic current consumption, } I_S = C_{PD} \ V_{CC} \ f + I_{CC} \ V_{CC}, \ \text{and the no load dynamic current consumption, } I_S = C_{PD} \ V_{CC} \ f + I_{CC} \ V_{CC}, \ \text{and the no load dynamic current consumption, } I_S = C_{PD} \ V_{CC} \ f + I_{CC} \ V_{CC}, \ \text{and the no load dynamic current consumption, } I_S = C_{PD} \ V_{CC} \ f + I_{CC} \ V_{CC}, \ \text{and the no load dynamic current consumption, } I_S = C_{PD} \ V_{CC} \ f + I_{CC} \ V_{CC}, \ \text{and the no load dynamic current consumption, } I_S = C_{PD} \ V_{CC} \ f + I_{CC} \ V_{CC}, \ \text{and the no load dynamic current consumption, } I_S = C_{PD} \ V_{CC} \ f + I_{CC} \ V_{CC}, \ \text{and the no load dynamic current consumption, } I_S = C_{PD} \ V_{CC} \ f + I_{CC} \ V_{CC}, \ \text{and the no load dynamic current consumption, } I_S = C_{PD} \ V_{CC} \ f + I_{CC} \ V_{CC}, \ \text{and the no load dynamic current consumption, } I_S = C_{PD} \ V_{CC} \ f + I_{CC} \ V_{$ 

#### Physical Dimensions inches (millimeters) 0.785 (19.939) MAX [14] [13] [12] [11] [10] [9] [8] 0.025 (0.635) RAD 0.220-0.310 (5.588-7.874) 1 2 3 4 5 6 7 0.290-0.320 0.005 0.200 (D.127) MIN (5.080) MAX 0.020-0.060 (7.366-8.128) GLASS 0.060 ±0.005 (1.524 ±0.127) 0.180 (0.508 - 1.524)MA 0.008-0.012 10° MAX (0.203-D.305) 0.310-0.410 D.018 ±0.003 0.125-0.200 0.098 (7.874 - 10.41)(0.457 ±0,076) (3.175-5.080) (2.489) MAX BOTH ENDS 0.100 ±0.010 0.150 (3.81) J14A (REV G) MIN Order Number MM54HC20J or MM54HC20J NS Package J14A 0.250 ± 0.010 (6.350 ± 0.254) 0.092 (2.337) DIA 0.030 MAX -0.125 - 0.150 0.075±0.015 (1.905±0.381) 0.050 ± 0.010 (1.270 - 0.254) TYP 0.325 +0.040 -0.015 (0.255 +1.016 -0.381 Order Number MM54HC20N NS Package N14A

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Datasheets for electronics components.

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